

Silicon PNP Power Transistors

2SB857 2SB858

DESCRIPTION

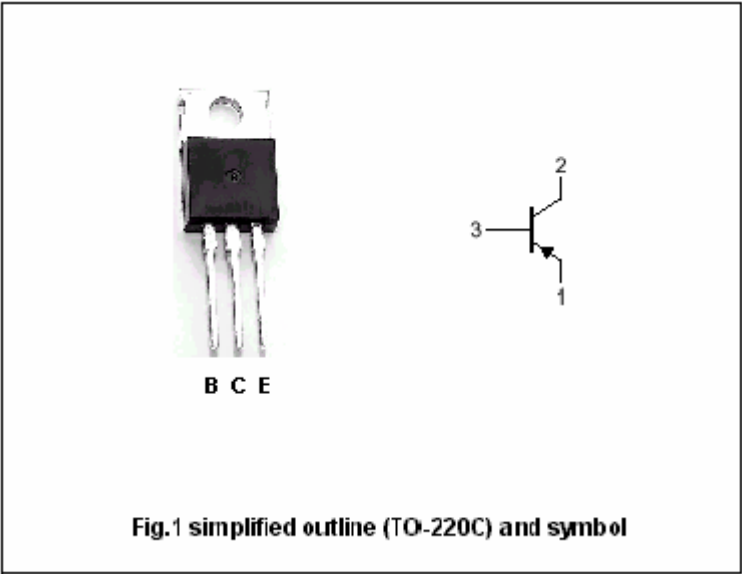
- With TO-220C package
- Complement to type 2SD1133/1134

APPLICATIONS

- Low frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Tc=25)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	-70	V
V_{CEO}	Collector-emitter voltage	2SB857	Open base	-50	V
		2SB858		-60	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-4	A
I_{CP}	Collector current-peak			-8	A
P_C	Collector power dissipation		$T_C=25$	40	W
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-45~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SB857	I _C =-50mA; R _{BE} =∞	-50			V
		2SB858		-60			
V _{(BR)CBO}	Collector-base breakdown voltage		I _C =-10 μA; I _E =0	-70			V
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =-10 μA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage		I _C =-2 A; I _B =-0.2 A			-1.0	V
V _{BE}	Base-emitter voltage		I _C =-1A; V _{CE} =-4V			-1.0	V
I _{CBO}	Collector cut-off current		V _{CB} =-50V; I _E =0			-1	μA
h _{FE-1}	DC current gain		I _C =-1A; V _{CE} =-4V	60		320	
h _{FE-2}	DC current gain		I _C =-0.1A; V _{CE} =-4V	35			
f _T	Transition frequency		I _C =-0.5A; V _{CE} =-4V		15		MHz

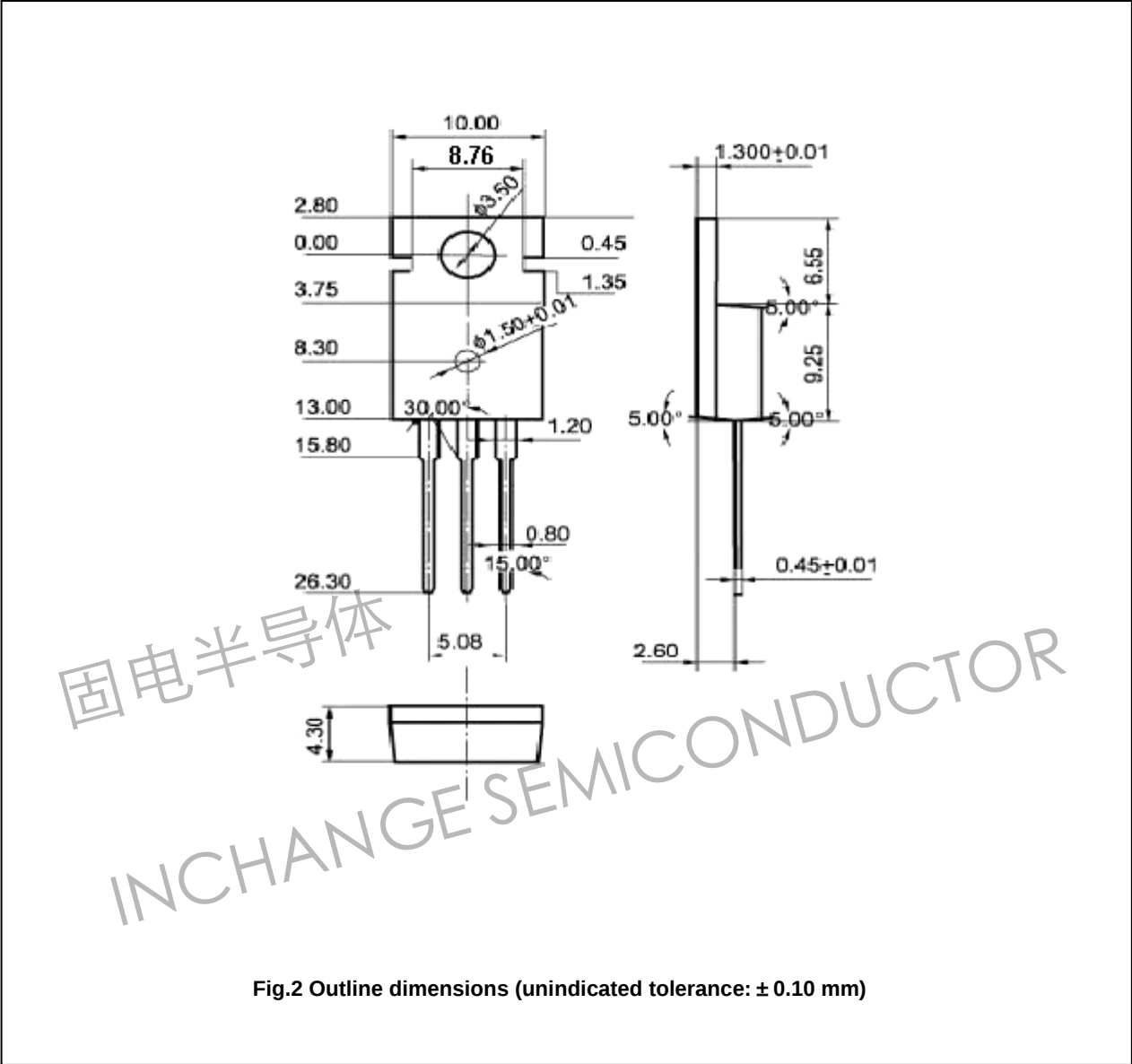
◆ h_{FE-1} classifications

B	C	D
60-120	100-200	160-320

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PACKAGE OUTLINE



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